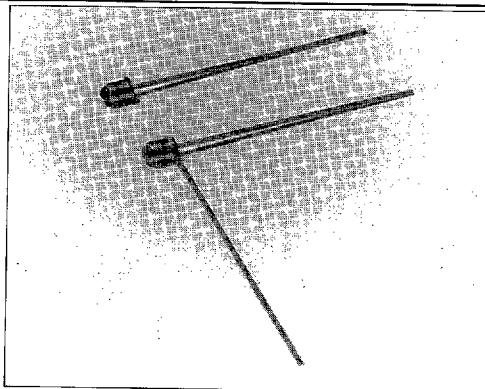


SD1440

Silicon Phototransistor

FEATURES

- Compact, metal can coaxial package
- 24° (nominal) acceptance angle
- Wide sensitivity ranges
- Wide operating temperature range (-55°C to +125°C)
- Mechanically and spectrally matched to SE1450 and SE1470 infrared emitting diodes



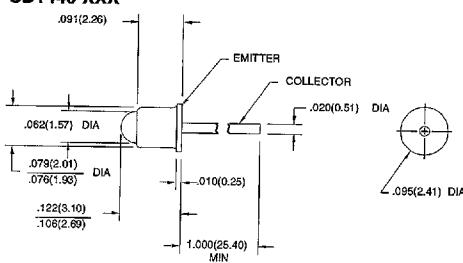
DESCRIPTION

The SD1440 is an NPN silicon phototransistor mounted in a glass lensed metal can coaxial package. The package may have a tab or second lead welded to the can as an optional feature (SD1440-XXXL). Both leads are flexible and may be formed to fit various mounting configurations.

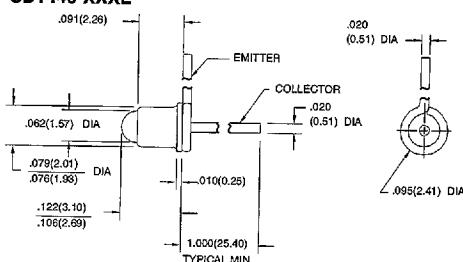
OUTLINE DIMENSIONS in inches (mm)

Tolerance 3 plc decimals $\pm 0.005(0.12)$
 2 plc decimals $\pm 0.020(0.51)$

SD1440-XXX



SD1440-XXXL



SD1440

Silicon Phototransistor

ELECTRICAL CHARACTERISTIC (25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Light Current SD1440-001, SD1440-001 L	I _L		0.7		mA	V _{CE} =5 V H=5 mW/cm ² (1)
SD1440-002, SD1440-002 L			1.5			
SD1440-003, SD1440-003 L			3.0			
SD1440-004, SD1440-004 L			6.0			
Collector Dark Current	I _{CBO}		100	nA		V _{CE} =10 V, H=0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	30			V	I _C =100 μA
Emitter-Collector Breakdown Voltage	V _{(BR)ECO}	5.0			V	I _E =100 μA
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		0.4		V	I _C =0.4 mA
Angular Response (2)	Ø		24		degr.	H=5 mW/cm ²
Rise And Fall Time	t _r , t _f		15		μs	I _F =Constant V _{CC} =5 V, I _E =1 mA R _L =1000 Ω

Notes

1. The radiation source is a tungsten lamp operating at a color temperature of 2870°K.
2. Angular response is defined as the total included angle between the half sensitivity points.

ABSOLUTE MAXIMUM RATINGS

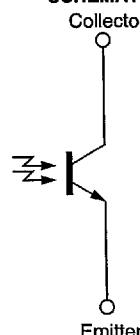
(25°C Free-Air Temperature unless otherwise noted)

Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Power Dissipation	75 mW (1)
Operating Temperature Range	-55°C to 125°C
Storage Temperature Range	-65°C to 150°C
Soldering Temperature (10 sec)	260°C

Notes

1. Derate linearly from 25°C free-air temperature at the rate of 0.71 mW/°C.

SCHEMATIC



SD1440

Silicon Phototransistor

SWITCHING TIME TEST CIRCUIT

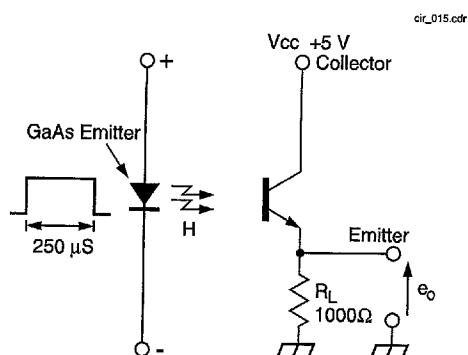


Fig. 1 Responsivity vs Angular Displacement

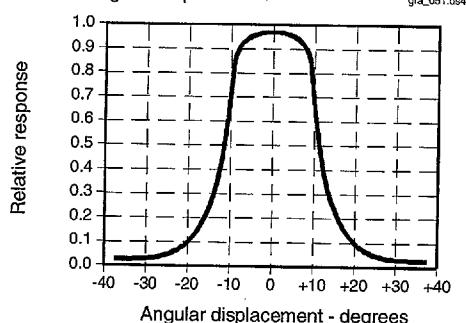
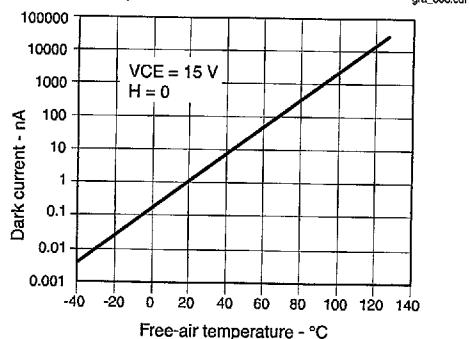


Fig. 3 Dark Current vs Temperature



SWITCHING WAVEFORM

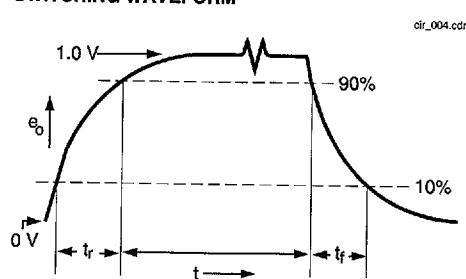


Fig. 2 Collector Current vs Ambient Temperature

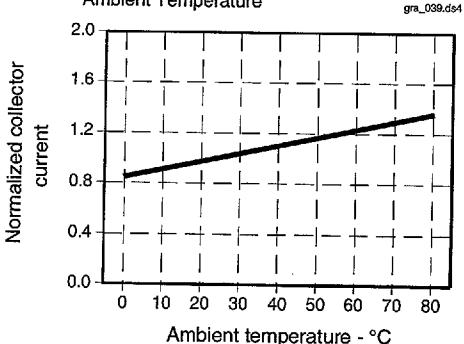
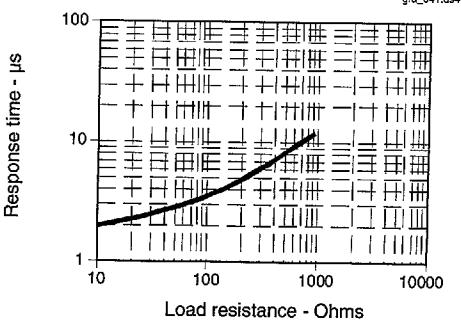


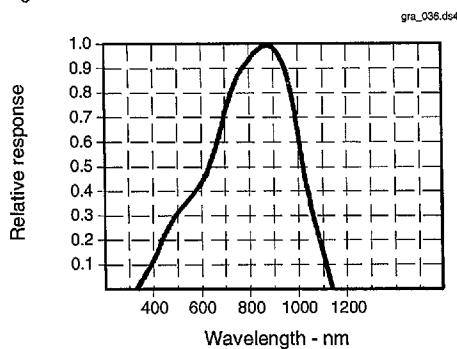
Fig. 4 Non-Saturated Switching Time vs Load Resistance



SD1440

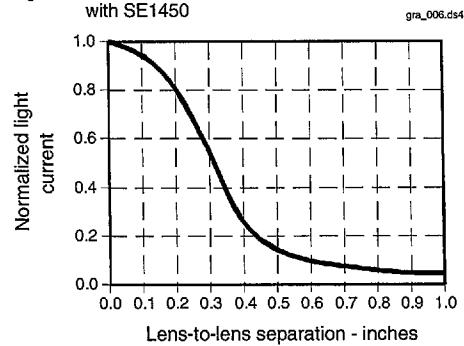
Silicon Phototransistor

Fig. 5 Spectral Responsivity



All Performance Curves Show Typical Values

Fig. 6 Coupling Characteristics with SE1450

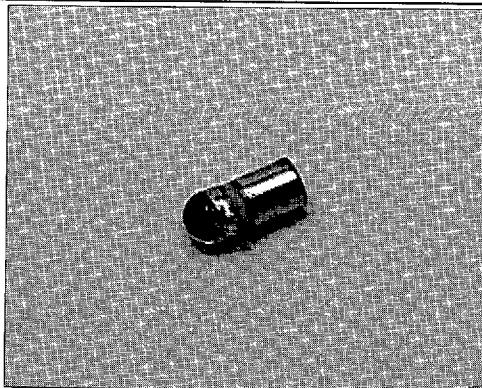


SD2440

Silicon Phototransistor

FEATURES

- Miniature, hermetically sealed, pill style, metal can package
- 48° acceptance angle
- Wide operating temperature range (-55°C to +125°C)
- Ideal for direct mounting to printed circuit boards
- Wide sensitivity ranges
- Mechanically and spectrally matched to SE2460 and SE2470 infrared emitting diodes



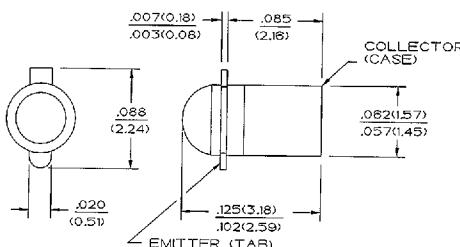
INFRAL-1.TIF

DESCRIPTION

The SD2440 is an NPN silicon phototransistor mounted in a hermetically sealed glass lensed metal can package. This package directly mounts in a double sided PC board.

OUTLINE DIMENSIONS in inches (mm)

Tolerance	3 plc decimals	$\pm 0.005(0.12)$
	2 plc decimals	$\pm 0.020(0.51)$



SD2440

Silicon Phototransistor

ELECTRICAL CHARACTERISTIC (25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Light Current SD2440-001	I _L		0.5		mA	V _{CE} =5 V H=20 mW/cm ² (1)
SD2440-002			2.0			
SD2440-003			4.0			
SD2440-004			7.0			
Collector Dark Current	I _{CEO}		100		nA	V _{CE} =10 V, H=0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	30			V	I _C =100 μA
Emitter-Collector Breakdown Voltage	V _{(BR)ECO}	5.0			V	I _E =100 μA
Collector-Emitter Saturation Voltage	V _{CE(sAT)}		0.4		V	I _C =I _E /2 H=20 mW/cm ²
Angular Response (2)	Ø		48		degr.	I _f =Constant
Rise And Fall Time	t _r , t _f		15		μs	V _{CC} =5 V, I _L =1 mA R _L =1000 Ω

Notes

1. The radiation source is a tungsten lamp operating at a color temperature of 2870°K.
2. Angular response is defined as the total included angle between the half sensitivity points.

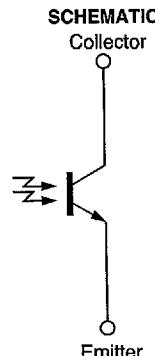
ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted)

Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Power Dissipation	125 mW (1)
Operating Temperature Range	-55°C to 125°C
Storage Temperature Range	-65°C to 150°C
Soldering Temperature (10 sec)	260°C

Notes

1. Derate linearly from 25°C free-air temperature at the rate of 1.19 mW/°C.



SD2440

Silicon Phototransistor

SWITCHING TIME TEST CIRCUIT

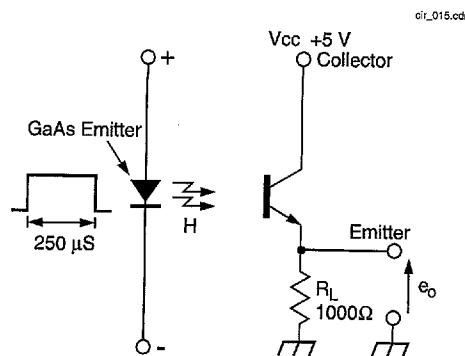


Fig. 1 Responsivity vs Angular Displacement

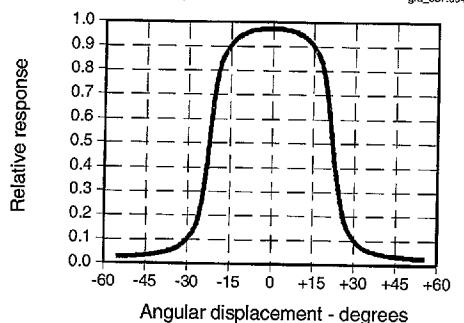
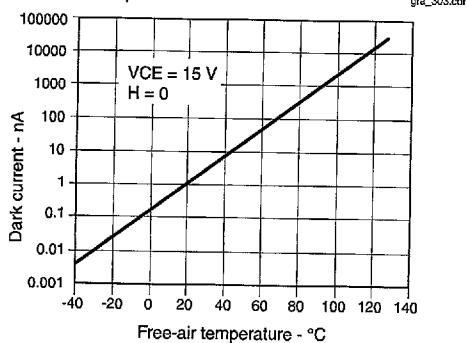


Fig. 3 Dark Current vs Temperature

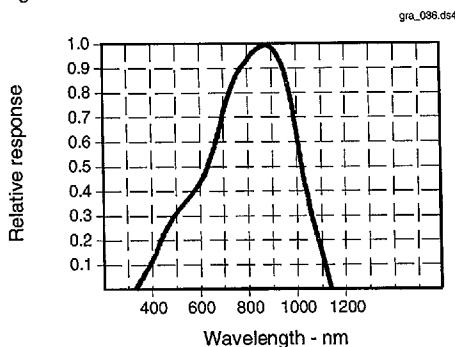


■ 4551830 0022532 472 ■
Honeywell

SD2440

Silicon Phototransistor

Fig. 5 Spectral Responsivity



All Performance Curves Show Typical Values

Fig. 6 Coupling Characteristics with SE2460

